NSCT817-25LT1G, NSCT817-40LT1G

General Purpose Transistors NPN Silicon

Features

• These are Pb–Free Devices

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	45	V
Collector – Base Voltage	V _{CBO}	50	V
Emitter – Base Voltage	V _{EBO}	5.0	V
Collector Current – Continuous	Ι _C	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta J A}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^{\circ}C$ Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA}	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

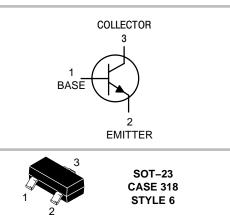
1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.

2. Alumina = 0.4 x 0.3 x 0.024 in 99.5% alumina.

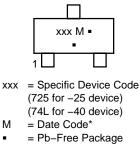


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MARKING DIAGRAM



(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
NSCT817-25LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
NSCT817-40LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
NSCT817-25LT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel
NSCT817-40LT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage $(I_C = -10 \text{ mA})$		V _{(BR)CEO}	45	_	-	V
Collector – Emitter Breakdown Voltage ($V_{EB} = 0$, $I_C = -10 \ \mu A$)		V _{(BR)CES}	50	-	-	V
Emitter – Base Breakdown Voltage $(I_E = -1.0 \ \mu A)$		V _{(BR)EBO}	5.0	_	-	V
Collector Cutoff Current $(V_{CB} = 20 V)$ $(V_{CB} = 20 V, T_A = 150^{\circ}C)$		I _{CBO}			100 5.0	nA μA
ON CHARACTERISTICS						
DC Current Gain (I _C = 100 mA, V _{CE} = 1.0 V) (I _C = 500 mA, V _{CE} = 1.0 V)	NSCT817–25 NSCT817–40	h _{FE}	160 250 40	- - -	400 600 -	_
Collector – Emitter Saturation Voltage $(I_C = 500 \text{ mA}, I_B = 50 \text{ mA})$		V _{CE(sat)}	-	-	0.7	V
Base – Emitter On Voltage ($I_C = 500$ mA, $V_{CE} = 1.0$ V)		V _{BE(on)}	-	-	1.2	V
SMALL-SIGNAL CHARACTERISTICS						
$\label{eq:current-Gain-Bandwidth Product} \begin{split} & (I_C = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ Vdc}, \text{ f} = 100 \text{ MHz}) \end{split}$		f _T	100	_	-	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)		C _{obo}	-	10	_	pF

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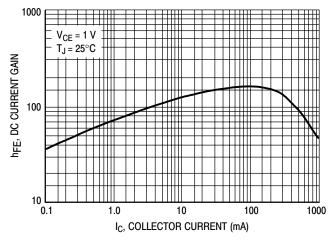
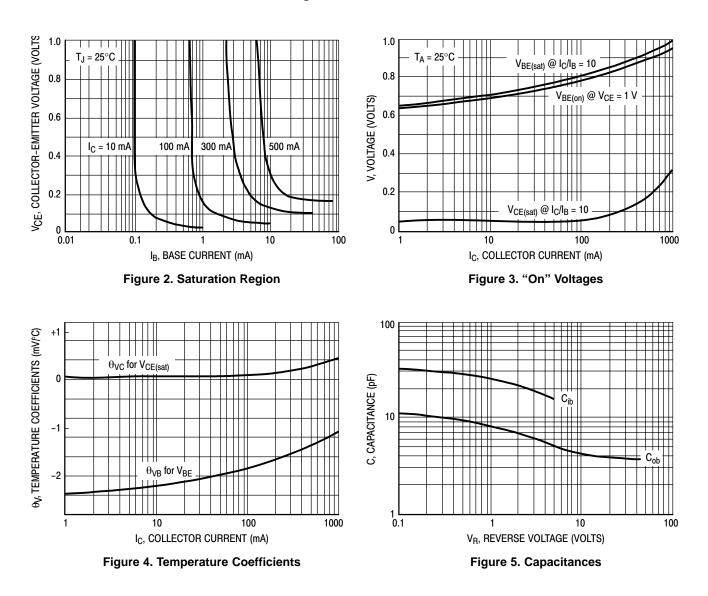


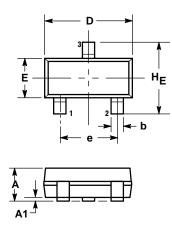
Figure 1. DC Current Gain

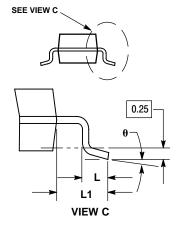


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PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AN





NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

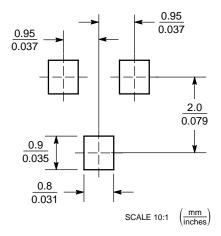
- 2. CONTROLLING DIMENSION: INCH
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 318-01 THRU -07 AND -09 OBSOLETE, NEW
- 318–01 THRU –07 AND –09 OBSOLETE, NEW STANDARD 318–08.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.89	1.00	1.11	0.035	0.040	0.044	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
b	0.37	0.44	0.50	0.015	0.018	0.020	
С	0.09	0.13	0.18	0.003	0.005	0.007	
D	2.80	2.90	3.04	0.110	0.114	0.120	
E	1.20	1.30	1.40	0.047	0.051	0.055	
е	1.78	1.90	2.04	0.070	0.075	0.081	
L	0.10	0.20	0.30	0.004	0.008	0.012	
L1	0.35	0.54	0.69	0.014	0.021	0.029	
HE	2.10	2.40	2.64	0.083	0.094	0.104	

STYLE 6: PIN 1. BASE

2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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